

FEATURES

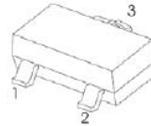
High density cell design for low $R_{DS(ON)}$
Voltage controlled small signal switch
Rugged and reliable
High saturation current capability

V_{DSS} 60 V
 I_D 340 mA
 $R_{DS(ON)}$ 1.7 m Ω

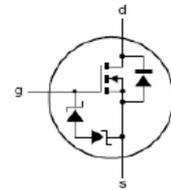
7002

SOT-23

1. GATE
2. SOURCE
3. DRAIN



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

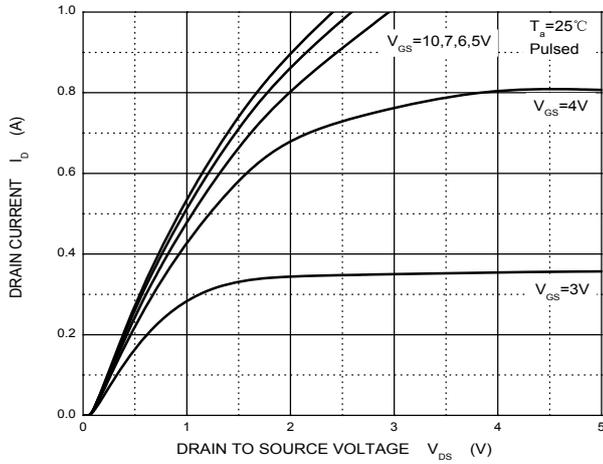
Symbol	Parameter	Value	Units
V_{DS}	Drain-Source voltage	60	V
V_{GS}	Gate-Source voltage	20	V
I_D	Drain Current	340	mA
P_D	Power Dissipation	0.35	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics

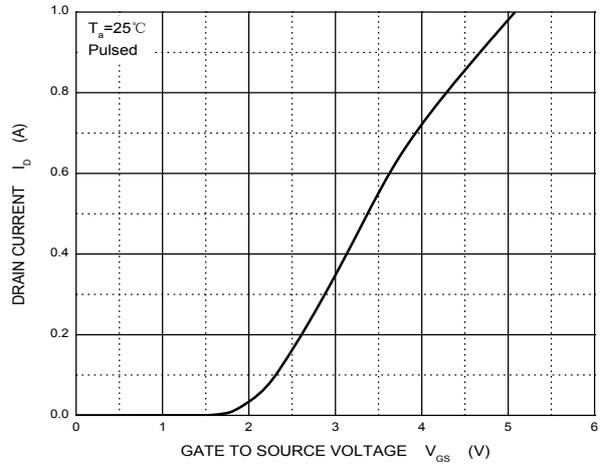
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage*	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	1		2.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate -Source leakage current	I_{GSS1}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
	I_{GSS2}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 200	nA
	I_{GSS3}	$V_{GS} = \pm 5V, V_{DS} = 0V$			± 100	nA
Drain-Source On-Resistance*	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 200mA$		1.7	5.3	Ω
		$V_{GS} = 10V, I_D = 500mA$			5	Ω
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 300mA$			1.5	V
Recovered charge	Q_r	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di_S/dt = -100A/\mu S$		30		nC
Dynamic Characteristics**						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	C_{oss}				30	pF
Reverse Transfer Capacitance	C_{rss}				10	pF
Switching Characteristics**						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega, R_{GS} = 50\Omega, R_L = 250\Omega$			10	ns
Turn-Off Delay Time	$t_{d(off)}$				15	ns
Reverse recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di_S/dt = -100A/\mu S$		30		ns
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	$I_{GS} = \pm 1mA$ (Open Drain)	± 21.5		± 30	V

RATING AND CHARACTERISTIC CURVES

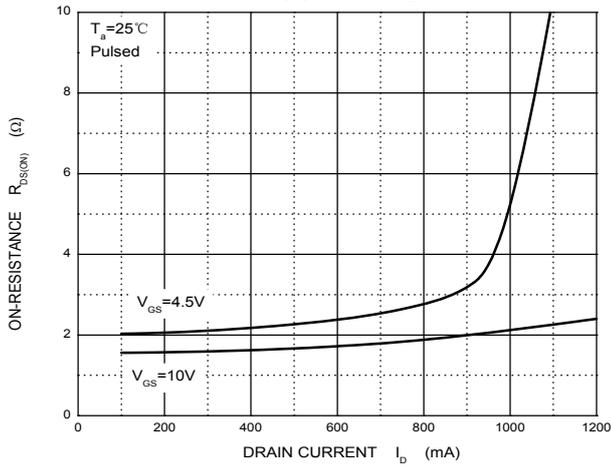
Output Characteristics



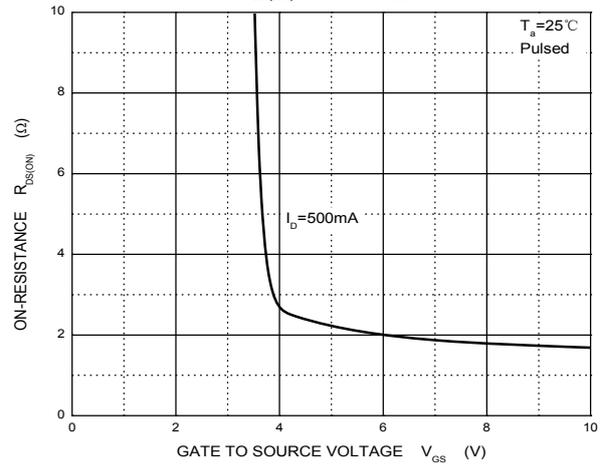
Transfer Characteristics



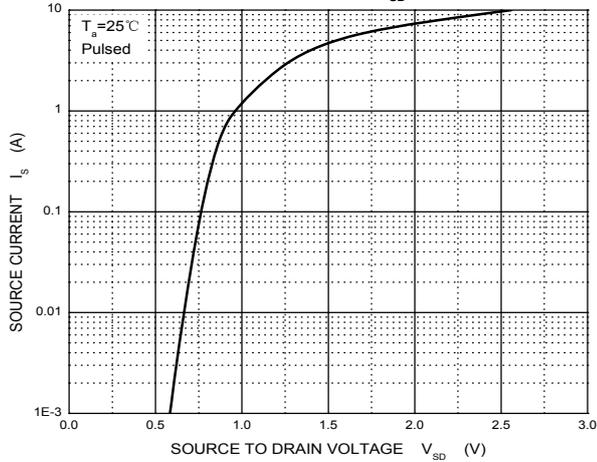
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}

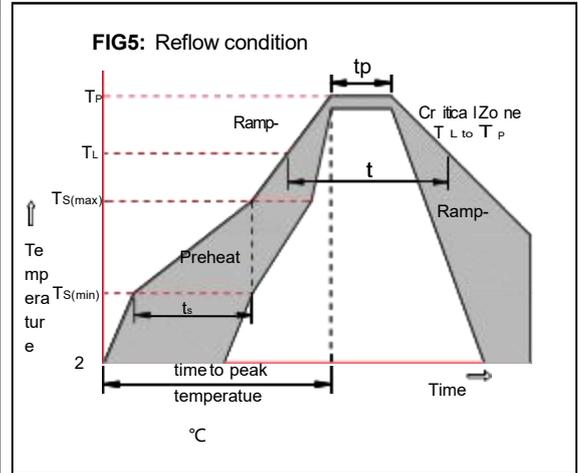


I_S — V_{SD}



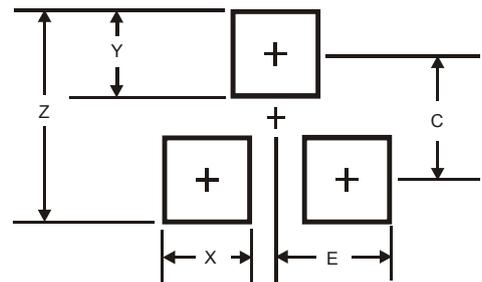
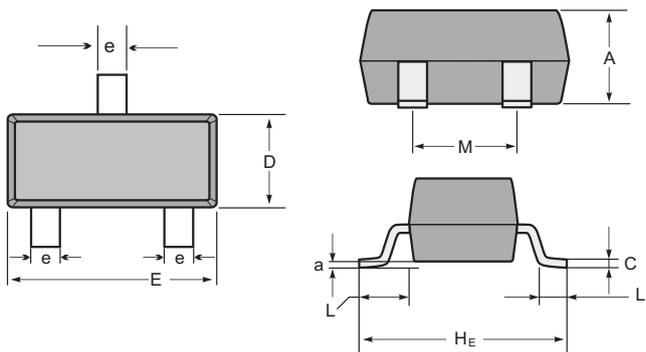
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max ($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature (T_L) (Liquid us)	+217 °C
	-Temperature (t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C



Package Dimensions & Suggested Pad Layout

SOT23



SOT-23 mechanical data

UNIT	A	C	D	E	HE	e	M	L	L1	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.10
		P1	4.00±0.10
		P2	2.00±0.10
		D0	1.55±0.10
		D1	1.05±0.10
		E	1.55±0.10
		F	3.60±0.10
		W	8.00±0.10
		A0	3.80±0.20
		B0	3.25±0.20
		K0	1.45±0.10
		T	0.25±0.05
		D2	178.0±3.0
		D3	55Min.
		D4	R24.0±3.0
G	R82.0±3.0		
I	13.0±2.0		
W1	11.0±3.0		
		Quantity: 3000PCS	

7" Reel		Symbol	Dimension (mm)		
		D2	178.0±3.0		
		D3	55Min.		
		D4	R24.0±3.0		
		G	R82.0±3.0		
		I	13.0±2.0		
		W1	11.0±3.0		
				Quantity: 3000PCS	